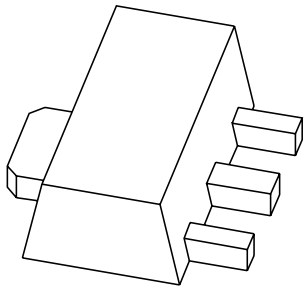


# DATA SHEET



## **BF620; BF622** NPN high-voltage transistors

Product data sheet  
Supersedes data of 1999 Apr 21

2004 Dec 14

## NPN high-voltage transistors

## BF620; BF622

## FEATURES

- Low current (max. 50 mA)
- High voltage (max. 300 V).

## APPLICATIONS

- Video output stages.

## DESCRIPTION

NPN high-voltage transistor in a SOT89 plastic package.  
PNP complements: BF621 and BF623.

## MARKING

| TYPE NUMBER | MARKING CODE |
|-------------|--------------|
| BF620       | DC           |
| BF622       | DA           |

## PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | emitter     |
| 2   | collector   |
| 3   | base        |

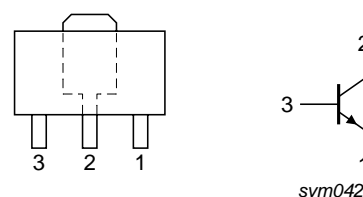


Fig.1 Simplified outline (SOT89) and symbol.

## ORDERING INFORMATION

| TYPE NUMBER | PACKAGE |  |         |
|-------------|---------|--|---------|
|             | NAME    | DESCRIPTION  | VERSION |
| BF620       | SC-62   | plastic surface mounted package; collector pad for good heat transfer; 3 leads | SOT89   |
| BF622       |         |  |         |

## NPN high-voltage transistors

## BF620; BF622

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

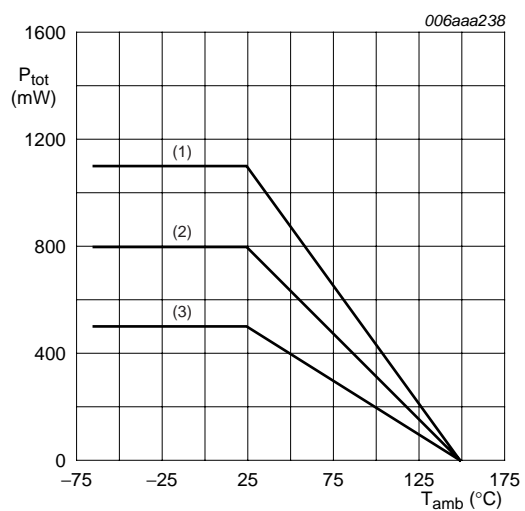
| SYMBOL           | PARAMETER                 | CONDITIONS               | MIN. | MAX. | UNIT |
|------------------|---------------------------|--------------------------|------|------|------|
| V <sub>CBO</sub> | collector-base voltage    | open emitter             | –    | 300  | V    |
|                  | BF620                     |                          |      | 250  | V    |
| V <sub>CEO</sub> | collector-emitter voltage | open base                | –    | 300  | V    |
|                  | BF620                     |                          |      | 250  | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector           | –    | 5    | V    |
| I <sub>C</sub>   | collector current (DC)    |                          | –    | 50   | mA   |
| I <sub>CM</sub>  | peak collector current    |                          | –    | 100  | mA   |
| I <sub>BM</sub>  | peak base current         |                          | –    | 50   | mA   |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C |      |      |      |
|                  |                           | note 1                   | –    | 0.5  | W    |
|                  |                           | note 2                   | –    | 0.8  | W    |
|                  |                           | note 3                   | –    | 1.1  | W    |
| T <sub>stg</sub> | storage temperature       |                          | –65  | +150 | °C   |
| T <sub>j</sub>   | junction temperature      |                          | –    | 150  | °C   |
| T <sub>amb</sub> | ambient temperature       |                          | –65  | +150 | °C   |

**Notes**

1. Device mounted on a printed-circuit board, single-sided copper, tin-plated and standard footprint.
2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.
3. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

## NPN high-voltage transistors

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- (1) FR4 PCB; 6 cm<sup>2</sup> mounting pad for collector.
- (2) FR4 PCB; 1 cm<sup>2</sup> mounting pad for collector.
- (3) FR4 PCB; standard footprint.

Fig.2 Power derating curves.

NPN high-voltage transistors

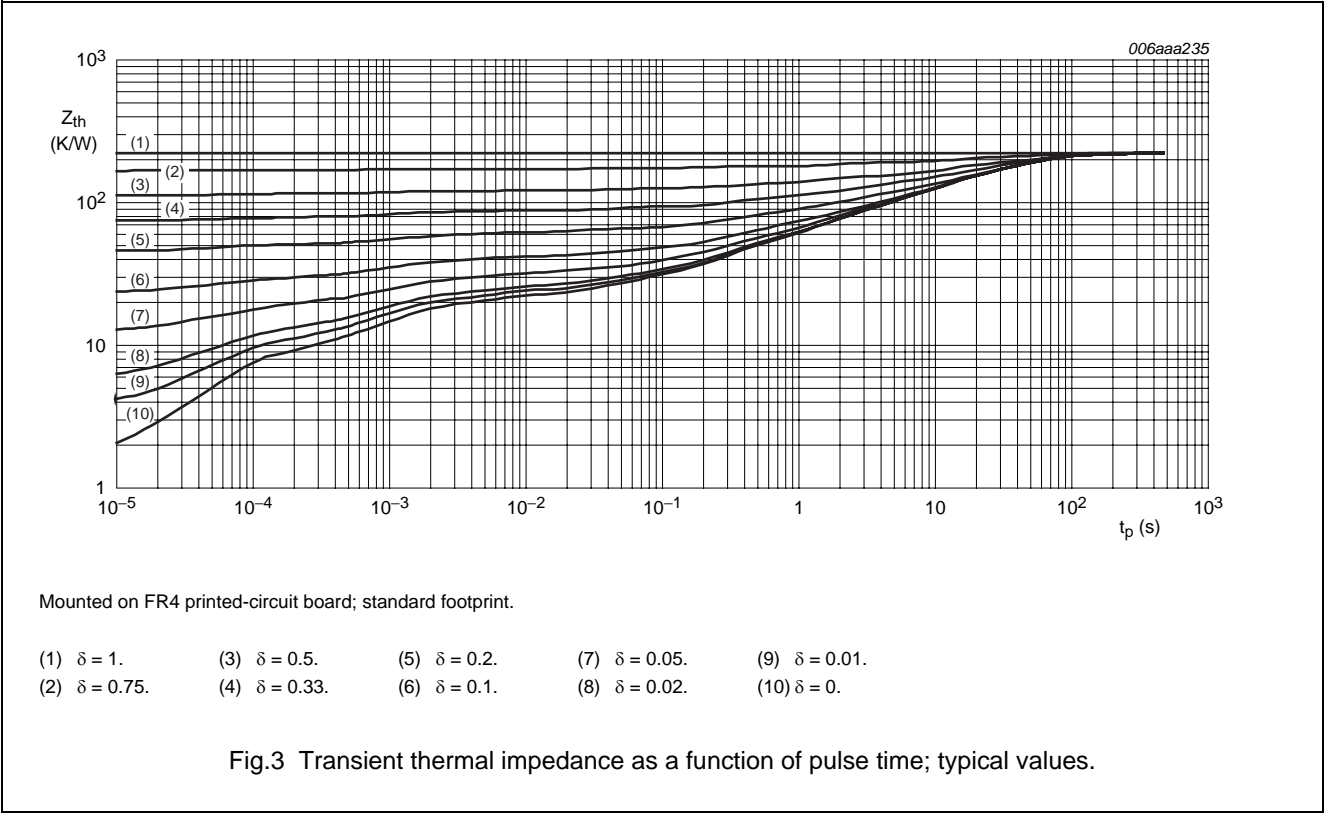
BF620; BF622

THERMAL CHARACTERISTICS

| SYMBOL        | PARAMETER   | CONDITIONS  | VALUE | UNIT |
|---------------|---|-------------|-------|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient         | in free air |       |      |
|               |   | note 1      | 250   | K/W  |
|               |   | note 2      | 156   | K/W  |
|               |   | note 3      | 113   | K/W  |
| $R_{th(j-s)}$ | thermal resistance from junction to soldering point |             | 30    | K/W  |

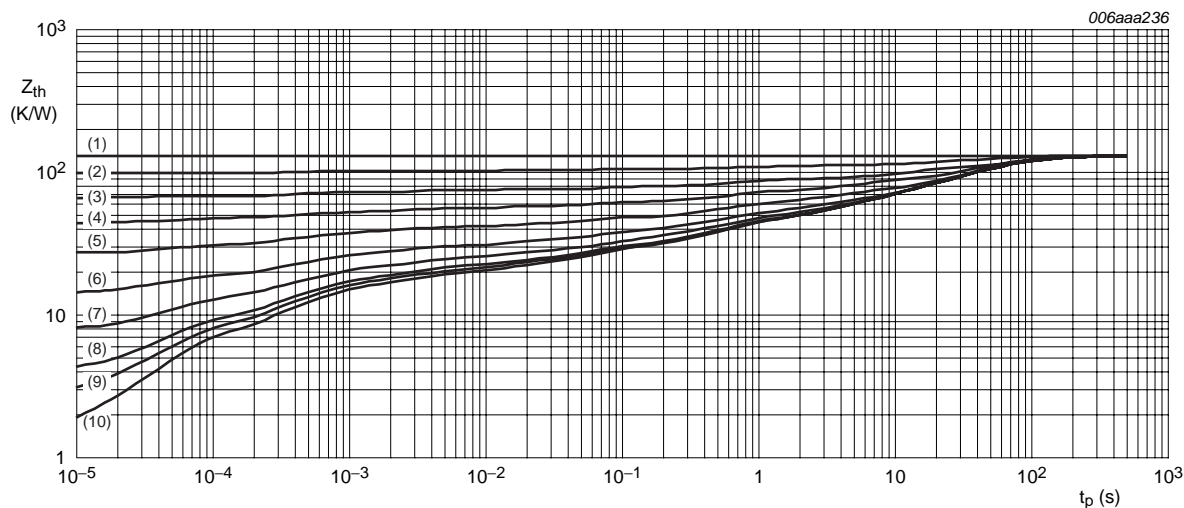
Notes

- 1. Device mounted on a printed-circuit board, single-sided copper, tin-plated and standard footprint.
- 2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.
- 3. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.



## NPN high-voltage transistors

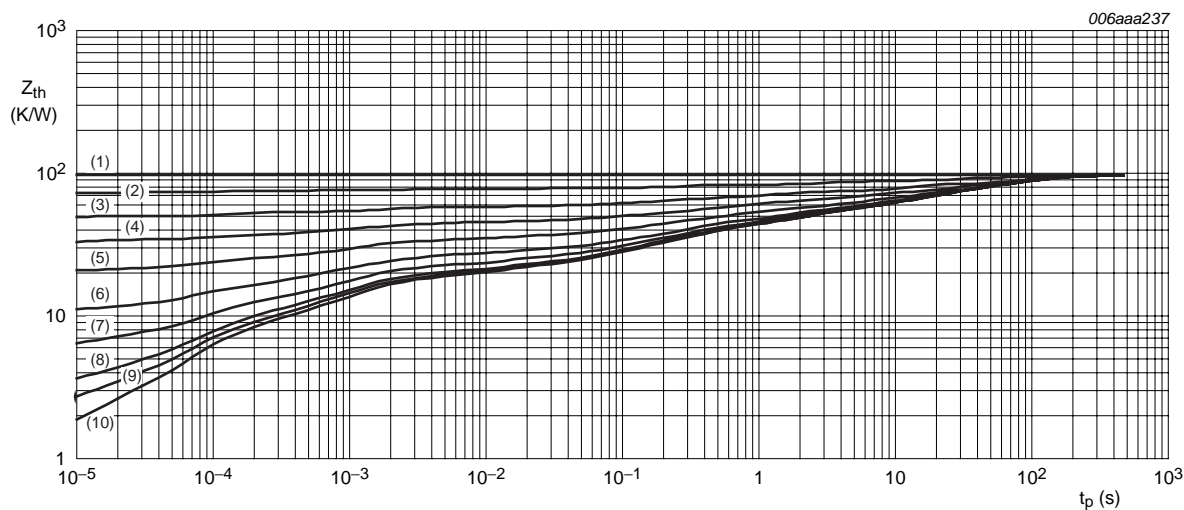
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Mounted on FR4 printed-circuit board; mounting pad for collector 1 cm<sup>2</sup>.

- |                      |                      |                     |                      |                      |
|----------------------|----------------------|---------------------|----------------------|----------------------|
| (1) $\delta = 1.$    | (3) $\delta = 0.5.$  | (5) $\delta = 0.2.$ | (7) $\delta = 0.05.$ | (9) $\delta = 0.01.$ |
| (2) $\delta = 0.75.$ | (4) $\delta = 0.33.$ | (6) $\delta = 0.1.$ | (8) $\delta = 0.02.$ | (10) $\delta = 0.$   |

Fig.4 Transient thermal impedance as a function of pulse time; typical values.



Mounted on FR4 printed-circuit board; mounting pad for collector 6 cm<sup>2</sup>.

- |                      |                      |                     |                      |                      |
|----------------------|----------------------|---------------------|----------------------|----------------------|
| (1) $\delta = 1.$    | (3) $\delta = 0.5.$  | (5) $\delta = 0.2.$ | (7) $\delta = 0.05.$ | (9) $\delta = 0.01.$ |
| (2) $\delta = 0.75.$ | (4) $\delta = 0.33.$ | (6) $\delta = 0.1.$ | (8) $\delta = 0.02.$ | (10) $\delta = 0.$   |

Fig.5 Transient thermal impedance as a function of pulse time; typical values.

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**CHARACTERISTICS**

$T_{\text{amb}} = 25\text{ °C}$  unless otherwise specified.

| SYMBOL             | PARAMETER                            | CONDITIONS  | MIN. | MAX. | UNIT |
|--------------------|--------------------------------------|---|------|------|------|
| $I_{\text{CBO}}$   | collector-base cut-off current       | $I_{\text{E}} = 0\text{ A}; V_{\text{CB}} = 200\text{ V}$                                 | –    | 10   | nA   |
|                    |                                      | $I_{\text{E}} = 0\text{ A}; V_{\text{CB}} = 200\text{ V}; T_{\text{j}} = 150\text{ °C}$   | –    | 10   | μA   |
| $I_{\text{EBO}}$   | emitter-base cut-off current         | $I_{\text{C}} = 0\text{ A}; V_{\text{EB}} = 5\text{ V}$                                   | –    | 50   | nA   |
| $h_{\text{FE}}$    | DC current gain                      | $I_{\text{C}} = 25\text{ mA}; V_{\text{CE}} = 20\text{ V}$                                | 50   | –    |      |
| $V_{\text{CEsat}}$ | collector-emitter saturation voltage | $I_{\text{C}} = 30\text{ mA}; I_{\text{B}} = 5\text{ mA}$                                 | –    | 600  | mV   |
| $C_{\text{re}}$    | feedback capacitance                 | $I_{\text{C}} = i_{\text{c}} = 0\text{ A}; V_{\text{CE}} = 30\text{ V}; f = 1\text{ MHz}$ | –    | 1.6  | pF   |
| $f_{\text{T}}$     | transition frequency                 | $I_{\text{C}} = -10\text{ mA}; V_{\text{CE}} = 10\text{ V}; f = 100\text{ MHz}$           | 60   | –    | MHz  |

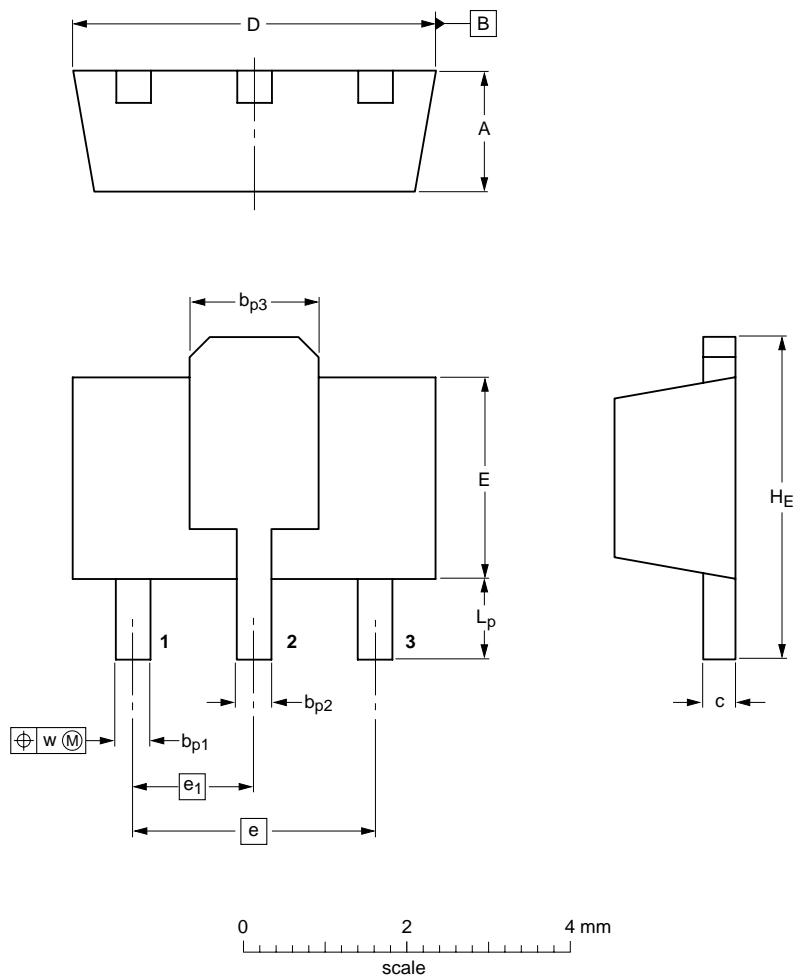
NPN high-voltage transistors

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PACKAGE OUTLINE


Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

| UNIT | A          | b <sub>p1</sub> | b <sub>p2</sub> | b <sub>p3</sub> | c            | D          | E          | e   | e <sub>1</sub> | H <sub>E</sub> | L <sub>p</sub> | w    |
|------|------------|-----------------|-----------------|-----------------|--------------|------------|------------|-----|----------------|----------------|----------------|------|
| mm   | 1.6<br>1.4 | 0.48<br>0.35    | 0.53<br>0.40    | 1.8<br>1.4      | 0.44<br>0.23 | 4.6<br>4.4 | 2.6<br>2.4 | 3.0 | 1.5            | 4.25<br>3.75   | 1.2<br>0.8     | 0.13 |

| OUTLINE<br>VERSION | REFERENCES |        |       |  | EUROPEAN<br>PROJECTION  | ISSUE DATE           |
|--------------------|------------|--------|-------|--|---|----------------------|
|                    | IEC        | JEDEC  | JEITA |  |   |                      |
| SOT89              |            | TO-243 | SC-62 |  |  | 04-08-03<br>06-03-16 |



## NPN high-voltage transistors

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## DATA SHEET STATUS

| DOCUMENT STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)</sup> | DEFINITION  |
|--------------------------------|-------------------------------|---|
| Objective data sheet           | Development                   | This document contains data from the objective specification for product development. |
| Preliminary data sheet         | Qualification                 | This document contains data from the preliminary specification.                       |
| Product data sheet             | Production                    | This document contains the product specification.                                     |

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